

c-axis Optical Conductivity in Cuprates

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We investigate the *c*-axis optical conductivity and d.c. resistivity of cuprate superconductors in the normal state. Assuming that the interlayer hopping is incoherent we express the conductivity with planar spectral functions obtained (i) from angle-resolved photoemission experiments, (ii) using marginal Fermi liquid ansatz, and (iii) with the finite-temperature Lanczos method for finite two-dimensional systems described by the *t*-*J* model. Here in the low doping regime a pseudo-gap opening in the density of states appears to be responsible for a semimetallic-like behavior of $\rho_c(T)$. In the optimally doped regime we find an anomalous relaxation rate $\tau_c^{-1} \propto \omega + \xi_c T$. Analytically this result is reproduced with the use of the marginal Fermi liquid ansatz for the self energy with parameters obtained from the exact diagonalization results.

I. INTRODUCTION

The CuO₂ planes are common to all cuprate superconductors and clearly determine most of the normal-state electronic properties. The quantity which most evidently displays the anisotropy of a particular material is the optical conductivity $\sigma(\omega, T)$ and the corresponding d.c. resistivity $\rho(T)$ [1].

We present here the theoretical analysis of $\sigma_c(\omega)$ within the standard planar *t*-*J* model and we additionally allow for the hopping between layers,

$$H = \sum_l H_l^{(t-J)} - t_c \sum_{lis} (c_{lis}^\dagger c_{l+1is} + \text{H.c.}). \quad (1)$$

where $H_l^{(t-J)}$ is the *t*-*J* model hamiltonian for the layer *l* and t_c is hopping matrix element between layers *l* and *l* ± 1. The interlayer hopping matrix element t_c is weak resulting in an incoherent *c*-axis transport.

In the limit of weak interlayer hopping $t_c \ll t$ it is straightforward to evaluate the dynamical *c*-axis conductivity $\sigma_c(\omega)$ using the linear response theory. The result is [2]

$$\begin{aligned} \sigma_c(\omega) = & \frac{\sigma_c^0}{\omega} \int d\omega' [f(\omega') - f(\omega' + \omega)] \\ & \times \frac{4\pi t^2}{N} \sum_{\mathbf{k}} A(\mathbf{k}, \omega') A(\mathbf{k}, \omega' + \omega), \end{aligned} \quad (2)$$

where $\sigma_c^0 = e_0^2 t_c^2 c_0 / \hbar a_0^2 t^2$ is a characteristic *c*-axis conductivity scale. Here e_0 is unit charge, a_0 and c_0 are *ab*-lattice constant and *c*-axis interlayer distance, respectively, N is the number of sites and $f(\omega)$ is the Fermi function. This approximation assumes the independent electron propagation in each layer, where electrons are described with the spectral function $A(\mathbf{k}, \omega)$. Eq. (2) could be compared with a related problem of interlayer hopping [3], where the corresponding expression for

$\sigma_c^n(\omega)$ is obtained as a convolution of the planar *density of states* (DOS) $N_p(\omega) = 2/N \sum_{\mathbf{k}} A(\mathbf{k}, \omega - \mu)$ and μ is the chemical potential,

$$\begin{aligned} \sigma_c^n(\omega) = & \frac{\sigma_c^0}{\omega} \int d\omega' [f(\omega') - f(\omega' + \omega)] \\ & \times \pi t^2 \mathcal{N}(\mu + \omega') \mathcal{N}(\mu + \omega' + \omega), \end{aligned} \quad (3)$$

appearing e.g. in disordered systems [3], together with a substitution for t_c in the definition of σ_c^0 with some average $\bar{t}_c$. In cuprates both alternatives have a justification, since the disorder introduced by dopants residing between layers modifies the hopping elements. Hence one can expect that the actual conductivity is a linear combination of σ_c and σ_c^n .

The knowledge of planar $A(\mathbf{k}, \omega)$ [or $N_p(\mu + \omega)$] should thus suffice for the evaluation of $\sigma_c(\omega)$.

II. RESULTS

We test first the Mott formula [3] for the d.c. resistivity $\rho_c(T) = 1/\sigma_c(\omega = 0, T)$ by inserting experimentally obtained photoemission spectra $\propto N_p(\omega)$ for La_{2-x}Sr_xCuO₄ [5]. The density of states is symmetrized around the Fermi energy and the result is presented in Fig. 1(a) for various values $x = 0.074 - 0.3$. Note that in the underdoped regime semimetallic behavior is qualitatively consistent with measured $\rho_c(T)$ [1]. In the optimally doped regime, however, experiments for $\rho_c(T)$ give linear *T*-dependence. For this regime therefore we take planar spectral functions consistent with the marginal Fermi liquid (MFL) concept [6], with parameters for the self energy taken from exact diagonalization [4]. In Fig. 1(b) we present results for $\rho_c(T)$ from Eq. (2) for the MFL scenario with full line and $\rho_c(T)$ from the Mott formula, Eq. (3), with dashed line.

Finally we present in Fig. 1(c) the d.c. resistivity $\rho_c(T)$ where we use numerical results for $A(\mathbf{k}, \omega)$ and $N_p(\omega)$,

for systems with $N = 16, 18, 20$ sites [4]. In the regime of intermediate and even higher doping $c_h \geq 3/16$ $\rho_c(T)$ is metallic-like for all T while for the underdoped limit due to the opening of the quasi-gap in the density of states $\rho_c(T)$ exhibits a semimetallic-like behavior.

To conclude, we point out that our approach gives a qualitative agreement with experiments in LSCO, what gives support to such a minimum model. Our results also confirm the general experimental observation that $\rho_c(T)$ changes from a metallic one to a semimetallic one, $d\rho_c(T)/dT < 0$, by decreasing doping.

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- [1] For a review see e.g. S. L. Cooper and K. E. Gray, in *Physical Properties of High Temperature Superconductors IV*, ed. by D. M. Ginsberg (World Scientific, Singapore, 1994), p.61.
 - [2] P. Prelovšek, A. Ramšak, and I. Sega, Phys. Rev. Lett. **81**, 3745 (1998).
 - [3] N. F. Mott and E. A. Davis, *Electronic processes in non-crystalline materials*, Clarendon Press, 1979.
 - [4] J. Jaklič and P. Prelovšek, Phys. Rev. B **49**, 5065 (1994); for a review see J. Jaklič and P. Prelovšek, cond-mat 9801333, to appear in Adv. Phys.; J. Jaklič and P. Prelovšek, Phys. Rev. B **55**, R7307 (1996); P. Prelovšek, J. Jaklič, and K. Bedell, Phys. Rev. B, to appear (1999).
 - [5] A. Ino *et al.*, Phys. Rev. Lett. **81**, 2124 (1998).
 - [6] C. M. Varma *et al.*, Phys. Rev. Lett. **63**, 1996 (1989).

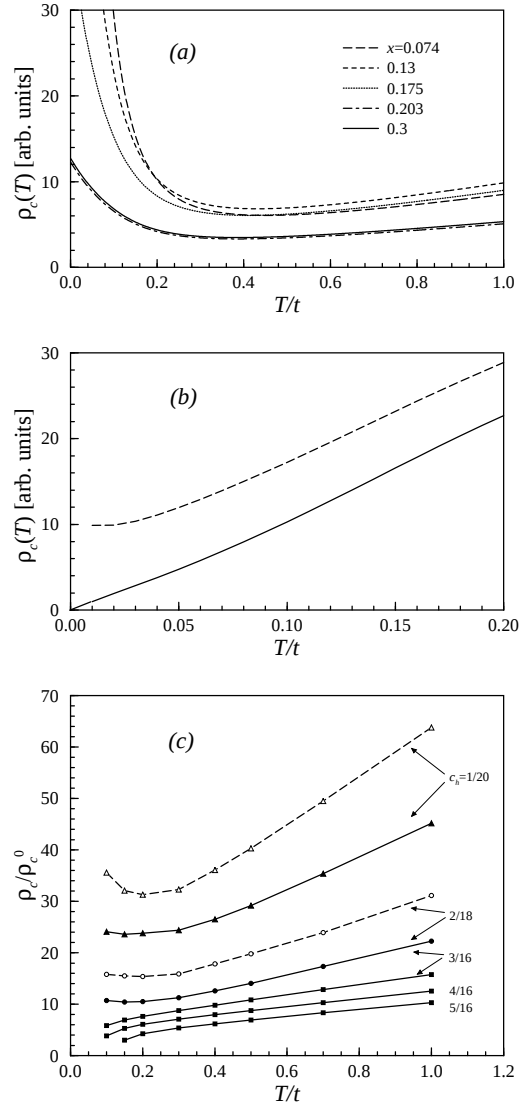


FIG. 1. $\rho_c(T)$: (a) from ARPES N_p for various doping x (b) from MFL $A_{\mathbf{k}}(\omega)$ (full line) and from N_p (dashed line) (c) from $A_{\mathbf{k}}(\omega)$ (full lines) and N_p (dashed lines) obtained with the t - J model and various doping c_h .